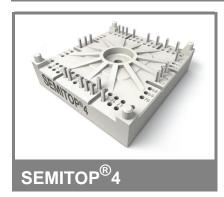
SK 35 DGDL 126 T



3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SK 35 DGDL 126 T

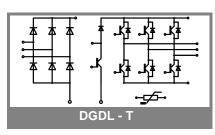
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperature sensor

Typical Applications*

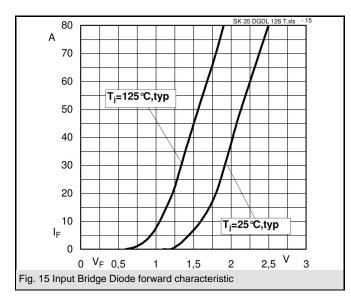
- Inverter up to 19 kVA
- Typ. motor power 7,5 kW
- 1) $V_{CE,sat}$, V_F = chip level value

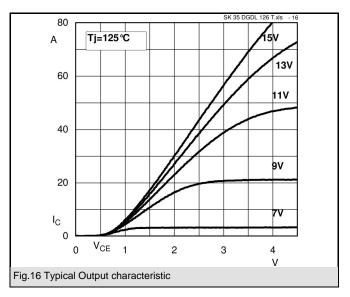


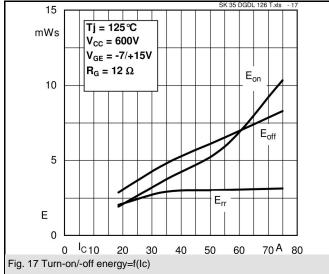
Absolute Maximum Ratings Ts = 25 °C, unless otherwise specifications of the state of the specification of the spec							
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V_{CES}		1200	V				
I _C	T _s = 25 (70) °C	52 (40)	Α				
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	70	Α				
V_{GES}		± 20	V				
T _j		-40 + 150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C	38 (29)	Α				
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$	70	Α				
T _j	·	-40 + 150	°C				
Rectifier							
V_{RRM}		1600	V				
I _F	T _s = 70 °C	35	Α				
I _{FSM} / I _{TSM}	$t_p = 10 \text{ ms}$, $\sin 180 ^{\circ}$, $T_i = 25 ^{\circ}\text{C}$	370	Α				
I ² t	$t_p = 10 \text{ ms}$, sin 180 °, $T_i = 25 \text{ °C}$	680	A²s				
T _j		-40 + 150	°C				
T _{sol}	Terminals, 10 s	260	°C				
T _{stg}		-40 +12 5	°C				
V _{isol}	AC, 1 min. / 1 s	2500 / 3000	V				

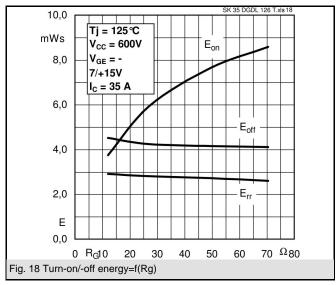
Characteristics		Ts = 25 °C,	Ts = 25 °C, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units		
IGBT - Inv	verter	·			-		
V_{CEsat}	I _C = 35 A, T _i = 25 (125) °C		1,7 (2)	2,1 (2,4)	V		
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_{C} = 1,5 \text{ mA}$	5	5,8	6,5	V		
V _{CE(TO)}	T _j = 25 °C (125) °C		1 (0,9)	1,2 (1,1)	V		
r _T	T _j = 25 °C (125) °C		20 (31)	26 (37)	mΩ		
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		2,5		nF		
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,13		nF		
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,11		nF		
$R_{th(j-s)}$	per IGBT		0,75		K/W		
t _{d(on)}	under following conditions		99		ns		
t _r	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		25		ns		
$t_{d(off)}$	I _C = 35 A, T _j = 125 °C		468		ns		
t_{f}	$R_{Gon} = R_{Goff} = 12 \Omega$		89		ns		
E _{on}	inductive load		3,7		mJ		
E_{off}			4,8		mJ		
Diode - Ir	verter,Chopper						
$V_F = V_{EC}$	I _F = 20 A, T _i = 25(125) °C		1,5 (1,5)	1,77 (1,77)	V		
V _(TO)	T _i = 25 °C (125) °C		(0,92)		V		
r _T	T _j = 25 °C (125) °C		(27,7)		mΩ		
$R_{th(j-s)}$	per diode		1,5		K/W		
I _{RRM}	under following conditions		58		Α		
Q _{rr}	I _F = 35 A, V _R = 600 V		9		μC		
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		3		mJ		
	di _{F/dt} = 1400 A/µs						
Diode - R	ectifier						
V_{F}	I _F = 25 A, T _i = 25() °C		1,1		V		
V _(TO)	T _i = 150 °C		0,8		V		
r _T	T _i = 150 °C		13		mΩ		
$R_{th(j-s)}$	per diode		1,25		K/W		
	tur sensor	•					
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω		
Mechanic	cal data						
w			60		g		
Ms	Mounting torque	2,5		2,75	Nm		

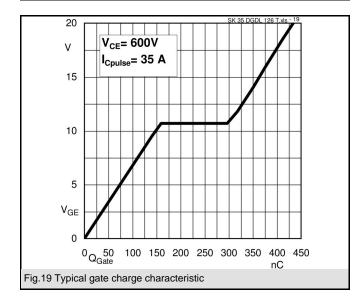
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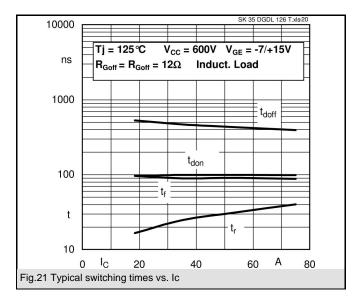


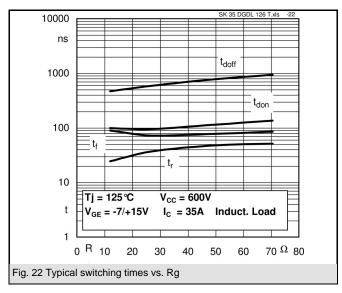


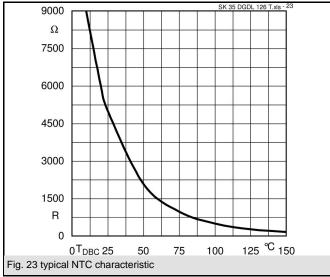


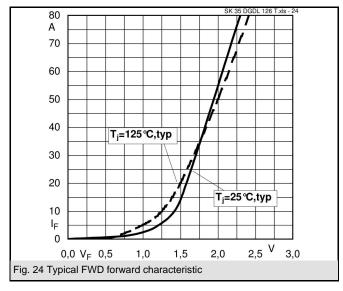


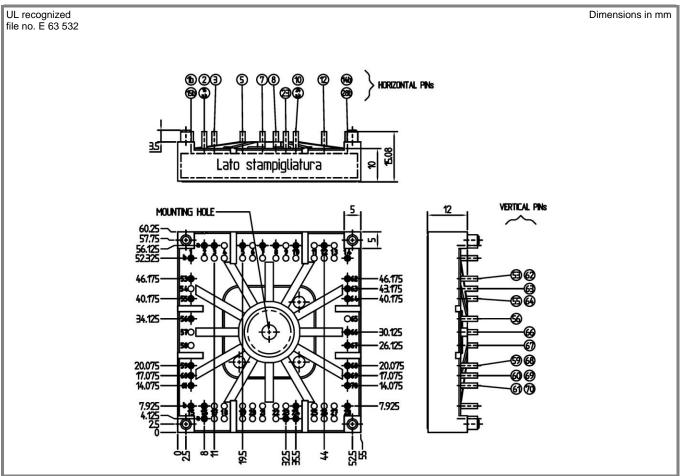
SK 35 DGDL 126 T



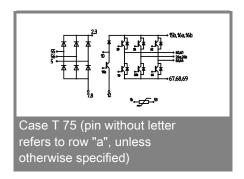








Case T 75 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.